MX0514 LDMOS TRANSISTOR

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140W, 28V High Power RF LDMOS FETs

Description

The MX0514 is a 140-watt capable, highly rugged, unmatched LDMOS FET, designed for wide-band commercial and industrial applications with frequencies HF to 1 GHz.

•Typical Performance (On Innogration fixture with device soldered):

 $V_{DD} = 28$ Volts, $I_{DQ} = 800$ mA, CW.

Frequency	Gp (dB)	P _{-1dB} (W)	η _D @P ₋₁ (%)
1000 MHz	18	140	60

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Suitable Applications

- 2-30MHz (HF or Short wave communication)
- 30-88MHz (Ground communication)
- 54-88MHz (TV VHF I)
- 88-108MHz (FM)
- 118 -140MHz (Avionics)

Table 1. Maximum Ratings

- 136-174MHz (Commercial ground communication)
- 160-230MHz (TV VHF III)
- 30-512MHz (Jammer, Ground/Air communication)
- 470-860MHz (TV UHF)
- 100kHz 1000MHz (ISM, instrumentation)

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Rating	Symbol	Value	Unit	
DrainSource Voltage	V _{DSS}	+95		
GateSource Voltage	V _{GS}	-10 to +10		
Operating Voltage	V _{dd}	+40		
Storage Temperature Range	Tstg	-65 to +150		
Case Operating Temperature	T _c	+150 °		
Operating Junction Temperature	T	+225		
Table 2. Thermal Characteristics			·	
Characteristic	Symbol	Value	Unit	
Thermal Resistance, Junction to Case	Rejc	0.4	°C/W	

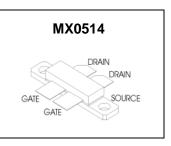
 $T_C = 85^{\circ}C$, $T_J = 200^{\circ}C$, DC test

Table 3. ESD Protection Characteristics

Test Methodology	Class	
Human Body Model (per JESD22A114)	Class 2	

Table 4. Electrical Characteristics ($T_A = 25$ °C unless otherwise noted)

Characteristic Symbol Min Typ Max Unit
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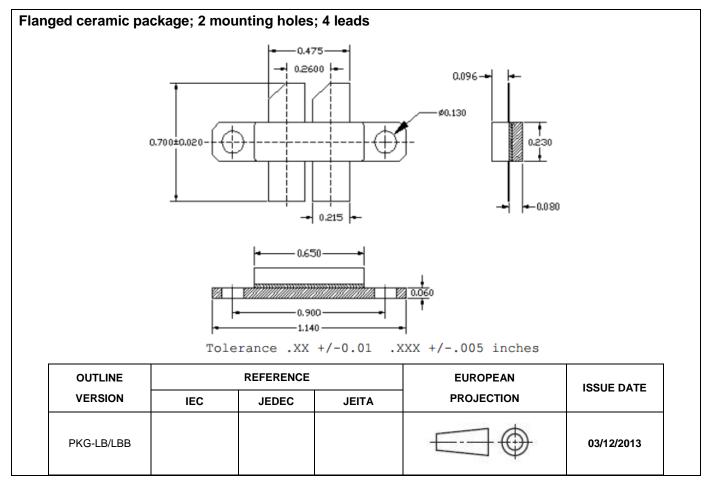


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DC Characteristics (per half section)					
Drain-Source Voltage	V	95			V
V_{GS} =0, I_{DS} =1.0mA	$V_{(BR)DSS}$	95			v
Zero Gate Voltage Drain Leakage Current	I _{DSS}			1	μΑ
$(V_{DS} = 75V, V_{GS} = 0 V)$					
Zero Gate Voltage Drain Leakage Current	I _{DSS}			1	μΑ
$(V_{DS} = 28 \text{ V}, V_{GS} = 0 \text{ V})$					
GateSource Leakage Current	_			1	A
$(V_{GS} = 10 \text{ V}, V_{DS} = 0 \text{ V})$	I _{GSS}			Γ	μΑ
Gate Threshold Voltage	V _{GS} (th)		2.2		V
$(V_{DS} = 28V, I_D = 400 \ \mu A)$	V _{GS} (III)		2.2		v
Gate Quiescent Voltage	V _{GS(Q)}		3.1		V
$(V_{\text{DD}}$ = 28 V, I_{D} = 800 mA, Measured in Functional Test)	V GS(Q)		5.1		v
Common Source Input Capacitance	C _{ISS}		70		pF
$(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$					
Common Source Output Capacitance	Coss		29.5		pF
$(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$	Coss		29.5		рі
Common Source Feedback Capacitance	C _{RSS}		1.1		pF
$(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$					
Functional Tests (In Demo Test Fixture, 50 ohm system) V _{DD} = 28 Vdc, I _{DQ} = 800 mA, f = 1000 MHz, CW Signal Measurements.					
Power Gain	Gp		18		dB
Drain Efficiency@P1dB	η⊳		60		%
1 dB Compression Point	P _{-1dB}		140		W
Input Return Loss			-7		dB
Load Mismatch (In Innogration Test Fixture, 50 ohm system): V _{DD} = 28 Vdc, I _{DQ} = 800 mA, f = 1000 MHz					
VSWR 20:1 at 140W pulse CW Output Power	No Device D	egradation			

DC Characteristics (per half section)

Package Outline



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Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2017/10/13	Rev 1.0	Product Datasheet Creation

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